

(6) A method for forming a thin film according to Claim 5, wherein the formation of the active region and the inactive region for the chemical vapor deposition is performed by forming a self-assembled film on the surface for forming the thin film having hydroxyl groups using a silane derivative represented by the general formula RSiX_3 (wherein R is a fluoroalkyl group in which terminal hydrogen of the alkyl group is replaced with fluorine, and X is an alkoxy group or halogen group); and performing ultraviolet irradiation on the self-assembled film through a photomask or performing electron beam irradiation on necessary parts of the self-assembled film so that the self-assembled film in a region for forming the active region for the chemical vapor deposition is removed.

(9) An electronic apparatus comprising a thin film formed by the above method, the thin film being used as an electrode.